



NPN SILICON RF TRANSISTOR NE68518 / 2SC5015

NPN EPITAXIAL SILICON RF TRANSISTOR FOR HIGH-FREQUENCY LOW-NOISE AMPLIFICATION 4-PIN SUPER MINIMOLD (18)

FEATURES

- High f_T : $f_T = 12$ GHz TYP. @ $V_{CE} = 3$ V, $I_C = 10$ mA, $f = 2$ GHz
- Low noise and high gain
- Low voltage operation
- 4-pin super minimold (18) package

★ ORDERING INFORMATION

Part Number	Quantity	Supplying Form
2SC5015	50 pcs (Non reel)	• 8 mm wide embossed taping • Pin 3 (Base), Pin 4 (Emitter) face the perforation side of the tape
2SC5015-T1	3 kpcs/reel	

Remark To order evaluation samples, contact your nearby sales office.
The unit sample quantity is 50 pcs.

ABSOLUTE MAXIMUM RATINGS ($T_A = +25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	9	V
Collector to Emitter Voltage	V_{CEO}	6	V
Emitter to Base Voltage	V_{EBO}	2	V
Collector Current	I_C	30	mA
Total Power Dissipation	P_{tot}	150	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +150	$^\circ\text{C}$

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.
Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.

ELECTRICAL CHARACTERISTICS (T_A = +25°C)

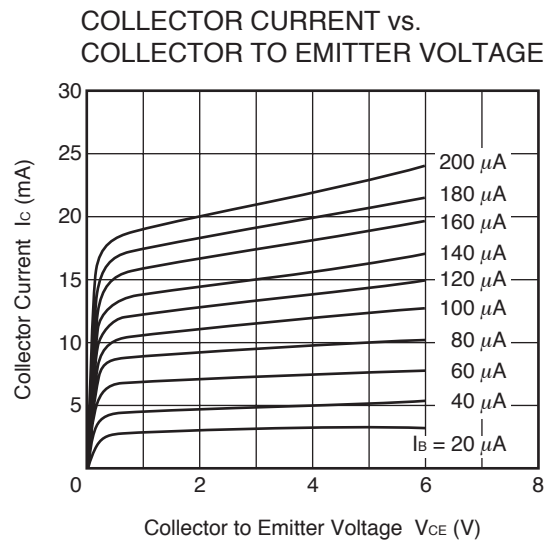
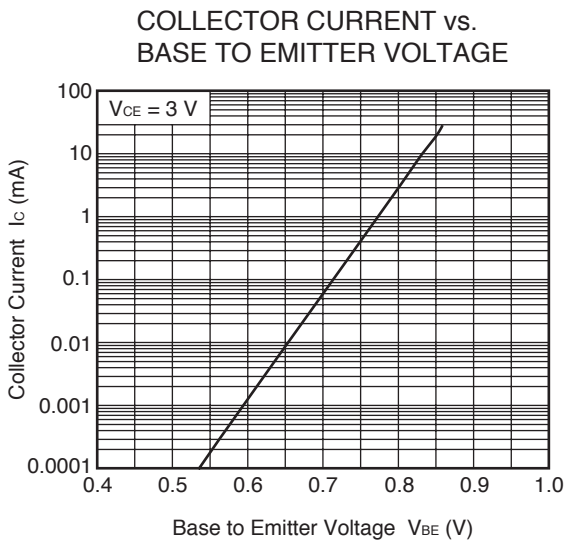
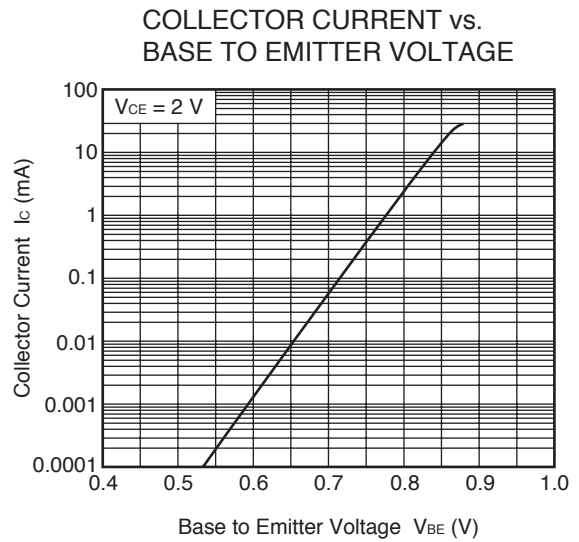
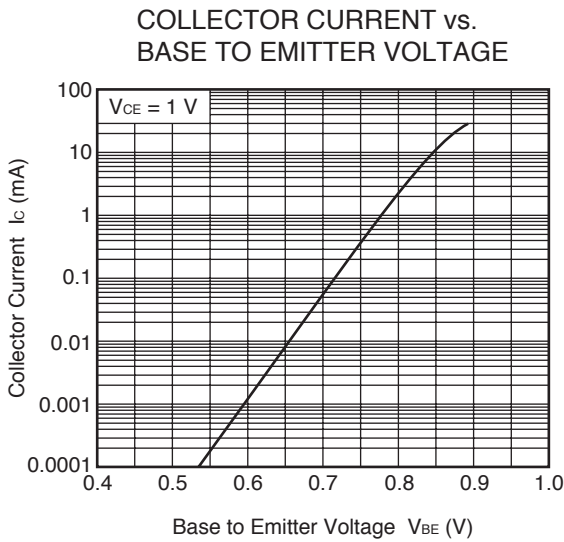
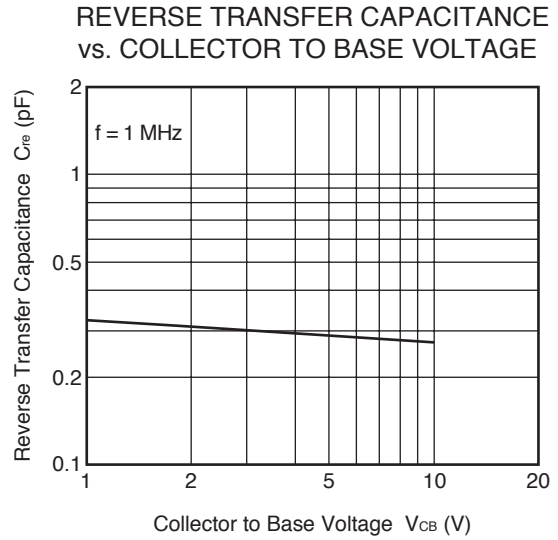
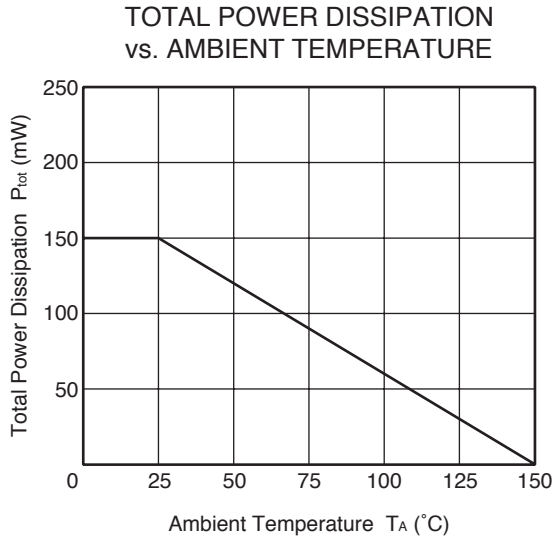
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics						
Collector Cut-off Current	I _{CBO}	V _{CB} = 5 V, I _E = 0 mA	-	-	0.1	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 1 V, I _C = 0 mA	-	-	0.1	μA
DC Current Gain	h _{FE} ^{Note 1}	V _{CE} = 3 V, I _C = 10 mA	75	-	150	-
RF Characteristics						
Gain Bandwidth Product	f _T	V _{CE} = 3 V, I _C = 10 mA, f = 2 GHz	-	12	-	GHz
Insertion Power Gain	S _{21e} ²	V _{CE} = 3 V, I _C = 10 mA, f = 2 GHz	9	11	-	dB
Noise Figure	NF	V _{CE} = 3 V, I _C = 3 mA, f = 2 GHz	-	1.5	2.5	dB
Reverse Transfer Capacitance	C _{re} ^{Note 2}	V _{CB} = 3 V, I _E = 0 mA, f = 1 MHz	-	0.3	0.5	pF

- Notes 1.** Pulse measurement: PW ≤ 350 μs, Duty Cycle ≤ 2%
2. Collector to base capacitance when the emitter grounded

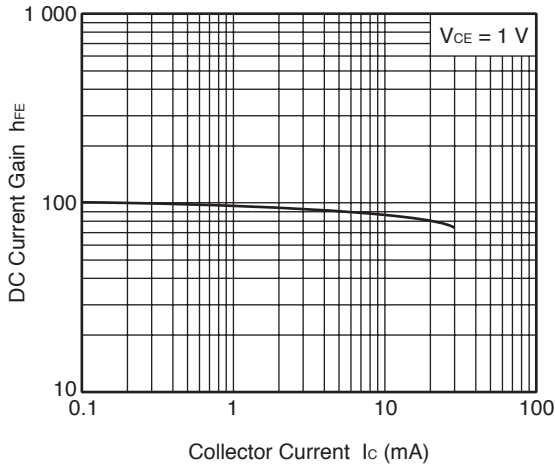
h_{FE} CLASSIFICATION

Rank	KB
Marking	T83
h _{FE} Value	75 to 150

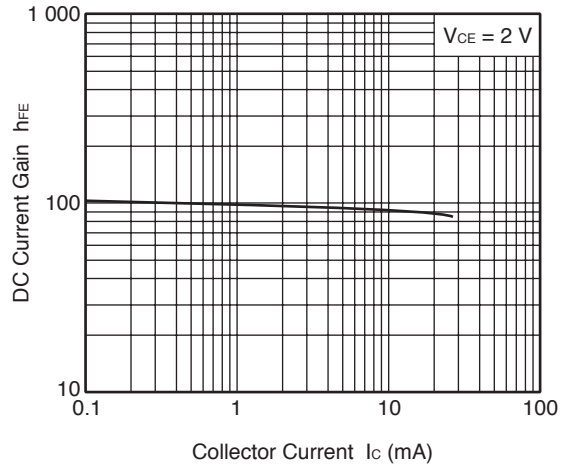
★ **TYPICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise specified)**



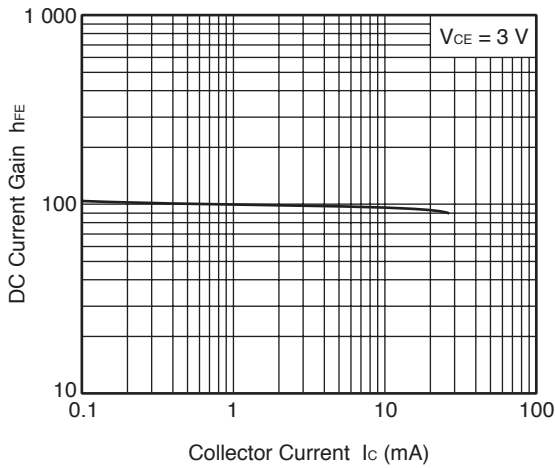
DC CURRENT GAIN vs. COLLECTOR CURRENT



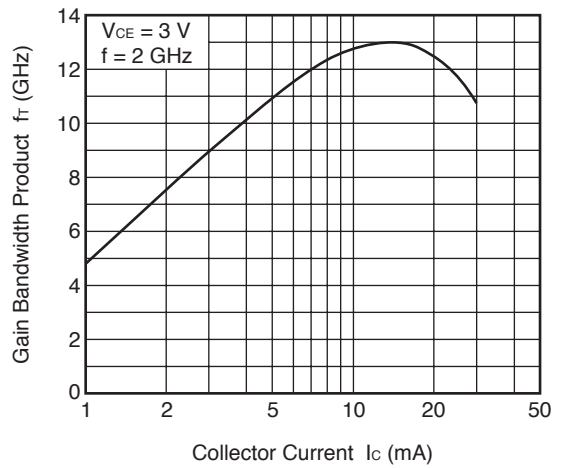
DC CURRENT GAIN vs. COLLECTOR CURRENT



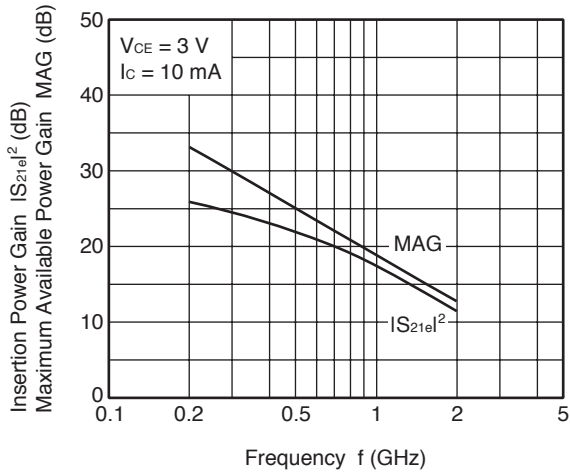
DC CURRENT GAIN vs. COLLECTOR CURRENT



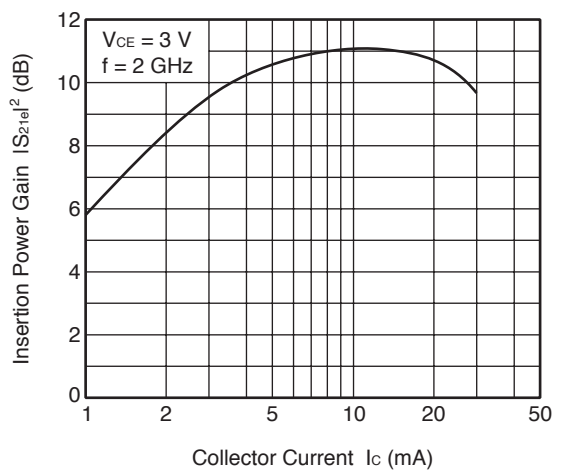
GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT

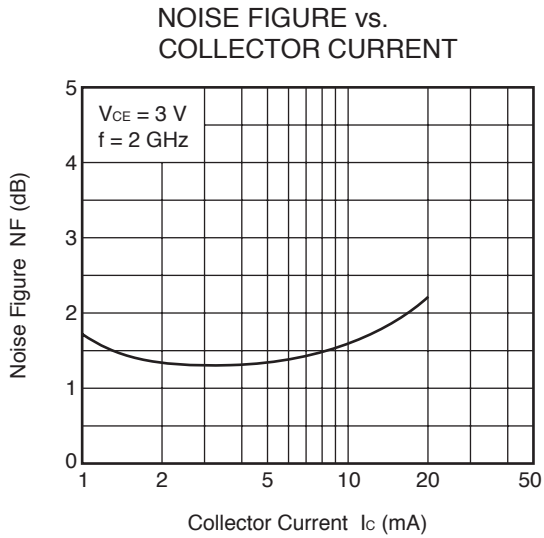


INSERTION POWER GAIN, MAG vs. FREQUENCY



INSERTION POWER GAIN vs. COLLECTOR CURRENT





Remark The graphs indicate nominal characteristics.

S-PARAMETERS

S-parameters/Noise parameters are provided on the NEC Compound Semiconductor Devices Web site in a form (S2P) that enables direct import to a microwave circuit simulator without keyboard input.

Click here to download S-parameters.

[RF and Microwave] → [Device Parameters]

URL <http://www.csd-nec.com/>

